



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

here application of

Docket No: Q72568

Takashi UDAGAWA

Appln. No.: 10/689,024

Group Art Unit: 2826

Confirmation No.: 4493

Examiner: Minh Loan Tran

Filed: October 21, 2003

For: GROUP-III NITRIDE SEMICONDUCTOR DEVICE, PRODUCTION METHOD
THEREOF AND LIGHT-EMITTING DIODE

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. §§ 1.97 and 1.98

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following: U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed (without a Statement Under 37 C.F.R § 1.97(e)) after the later of three months from the application's filing date and the mailing date of the first Office Action on the merits, but before a Final Office Action, Notice of

INFORMATION DISCLOSURE STATEMENT
U.S. Application No.: 10/689,024

Q72568

Allowance, or an action that otherwise closes prosecution in the application (whichever is earlier), and therefore a check for the fee of \$180.00 under 37 C.F.R. § 1.17(p) is attached.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account. A duplicate copy of this paper is attached.

Respectfully submitted,



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WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: May 27, 2005

Substitute for Form 1449 A & B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				<i>Complete if Known</i>	
				Application Number	10/689,024
				Confirmation Number	4493
				Filing Date	October 21, 2003
				First Named Inventor	Takashi UDAGAWA
				Art Unit	2826
				Examiner Name	Minh Loan Tran
				Attorney Docket Number	Q72568
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US 6,069,021		05-30-2000	TERASHIMA et al.
		US			
		US			
		US			
		US			
		US			
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	10-56202		02-24-1998	SHOWA DENKO KK	Abstract
		JP	55-3834		01-26-1980		Abstract
		JP	10-107315		04-24-1998	SHOWA DENKO KK	Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		Isamu AKASAKI (compiler), "Advanced Electronics Series, I-21, Group-III Nitride Semiconductor", 1 st edition, pp. 288-289, Baifukan (December 8, 1999)	Abstract
		Isamu AKASAKI et al., "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga _{1-x} Al _x N (0<x≤0.4) Films Grown on Sapphire Substrate by MOVPE"; Journal of Crystal Growth (the Netherlands); Vol. 98, pp. 209-219 (1989)	
		Isamu AKASAKI (compiler), "Advanced Electronics Series, I-21, Group-III Nitride Semiconductor"; 1 st edition, pp. 211-213, Baifukan (December 8, 1999)	Abstract

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.